

IN THE CLAIMS

Claims 9 and 13 had previously been canceled without prejudice.

Please add new claim 123.

Please enter the following claims:

Sub E¹

8. (Twice Amended) A gate electrode comprising:
- a gate layer disposed above a substrate, said gate layer having a substantially level upper surface;
 - a conductive layer disposed over said gate layer, said conductive layer extending beyond edges of said gate layer;
 - thin first spacers disposed in contact with opposite sides of said gate layer and below said conductive layer; and
 - thick second spacers disposed in contact with said thin first spacers, said thick second spacers having a uniform width throughout its height.

Sub E²

10. (Twice Amended) The gate electrode of claim 8 wherein said gate layer comprises polysilicon.
11. (Once Amended) The gate electrode of claim 10 wherein said conductive layer comprises polycide.

D2
comd

~~E~~
12. (Twice Amended) The gate electrode of claim 8 wherein said thin first spacers comprise oxide.

Subt E³

D3

~~E~~
14. (Twice Amended) The gate electrode of claim 11 wherein said polycide comprises titanium salicide (TiSi₂).

Subt E⁴

✓
D4

~~E~~
123. (New) The gate electrode of claim 8 wherein said thick second spacers comprise nitride.
